Alloying Sb into all inorganic lead-free $CsBi_3I_{10}$ for improving the crystal growth and photovoltaic performance

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Table S1. Photovoltaic performance of $Cs(Bi_xSb_{1-x})_3I_{10}$ devices prepared from DMF and DMSO mixed solvent with volume ratio of 9:1.

Sample	$V_{\rm oc}\left({ m V} ight)$	$J_{\rm sc}$ (mA cm ⁻²)	FF (%)	PCE (%)
CsBi ₃ I ₁₀	0.47	2.55	38.7	0.45
$Cs(Bi_{0.7}Sb_{0.3})_3I_{10}$	0.74	2.57	32.6	0.62
$Cs(Bi_{0.5}Sb_{0.5})_3I_{10}$	0.65	0.99	25.6	0.16

Table S2. Photovoltaic performance of $Cs(Bi_{0.7}Sb_{0.7})_3I_{10}$ devices prepared from mixed DMF/DMSO solvents with different DMSO volume ratios.

DMSO concentration	$V_{\rm oc}$ (V)	$J_{\rm sc}$ (mA cm ⁻²)	FF (%)	PCE (%)
0%	0.69	0.52	27.9	0.10
30%	0.72	3.50	31.7	0.80
50%	0.72	3.93	32.5	0.92
100%	0.75	4.62	30.7	1.06

Table S3. Photovoltaic performance of $Cs(Bi_xSb_{1-x})_3I_{10}$ devices prepared from 100 vol% DMSO solvent.

x (Sb content)	$V_{\rm oc}$ (V)	$J_{\rm sc}$ (mA cm ⁻²)	FF (%)	PCE (%)
0	0.46	2.89	41.8	0.55
0.1	0.54	1.26	30.8	0.21
0.2	0.63	2.50	29.2	0.46
0.25	0.73	3.21	30.7	0.72
0.3	0.75	4.62	30.7	1.06
0.35	0.75	4.24	30.2	0.96
0.4	0.75	4.18	29.0	0.91



Fig. S1. SEM images of Cs(Bi_{1-x}Sb_x)₃I₁₀ films (x=0, 0.1, 0.2, 0.3, 0.4, 0.5) from DMF/DMSO (9:1 v/v) solvent. (Scale bar: 500 nm)



Fig. S2. SEM images of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ film from different scanning scales.



Fig. S3. XRD patterns of $Cs(Bi_{1-x}Sb_x)_3I_{10}$ thin films (x = 0, 0.1, 0.2, 0.3, 0.4, 0.5).



Fig. S4. Uv-vis absorbance spectra of $Cs(Bi_{1-x}Sb_x)_3I_{10}$ thin films (x = 0, 0.1, 0.2, 0.3, 0.4, 0.5).



Fig. S5. Tauc-plots derived from optical absorbance of $Cs(Bi_{1-x}Sb_x)_3I_{10}$ thin films (x = 0, 0.1, 0.2, 0.3, 0.4, 0.5) assuming direct transition.



Fig. S6. Tauc-plots derived from optical absorbance of $Cs(Bi_{1-x}Sb_x)_3I_{10}$ thin films (x = 0, 0.1, 0.2, 0.3, 0.4, 0.5) assuming indirect transition.



Fig. S7. Calculated bandgaps vs different Sb-substitution ratios.



Fig. S8. SEM images of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ film from pure 100 vol% DMF solvent.



Fig. S9. SEM images of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ films from solvents with different DMSO volume ratios. (Scale bar: 500 nm)



Fig. S10. XRD patterns of $Cs(Bi_{0.7}Sb_{0.3})_3I_{10}$ films synthesized from solvents with different DMSO volume ratios.

Fig. S11. Steady-state PL (a) and time resolved PL (TRPL) (b) spectra of CBSI-3 films prepared from low-DMSO-contained solvent (DMSO 30 vol%) and high-DMSO-contained solvent (DMSO 100 vol%).

Fig. S12. J-V plots of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ devices from solvents with different DMSO volume ratios with the device structure of ITO/PEDOT/CBSI-3/PCBM/BCP/Ag.

Fig. S13. EQE curves of $Cs(Bi_{1-x}Sb_x)_3I_{10}$ solar cells from 100 vol% DMSO solvent with the structure of ITO/PEDOT/CSBI/PCBM/BCP/Ag.

Fig. S14. J-V plots of $Cs(Bi_{0.7}Sb_{0.3})_3I_{10}$ devices from different precursor solution concentrations, and CSBI-3 films here were synthesized from 100 vol% DMSO solvent.

Fig. S15. J-V plots of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ solar cells with CSBI-3 films being synthesized from DMF/DMSO mixed solvent with volume ratio of 9:1 and post-annealed at different temperatures.

Fig. S16. Cross-sectional SEM image of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀/PCBM heterojuntion film as the active layer on the ITO/PEDOT substrate. The Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ film was synthesized from 0.31 M precursor solution using pure 100 vol% DMSO as solvent.

Fig. S17. SEM images of Cs(Bi_{0.7}Sb_{0.3})₃I₁₀ films on PTAA and PEDOT substrates with different DMSO volume ratios. (Scale bar: 300 nm)

Fig. S18. Power output tracking by continuous measuring the *J-V* curves in air under ambient conditions.

Fig. S19. Storage stability of CSBI-3 solar cell tested over a 14-day period in an Arfilled glovebox.

Fig. S20. Light-soaking stability of CSBI-3 solar cell tested over a 7-day period in an Ar-filled glovebox.